

ABSTRACT OF THE DISCLOSURE

The image reading device of the present invention includes (i) a sensor substrate which functions as a photoelectric transfer element having a photodetecting TFT and a pixel capacitor and (ii) a driving IC for applying a voltage to a gate electrode of the photodetecting TFT so as to drive the photodetecting TFT into an ON state or an OFF state. The driving IC applies a voltage, whose polarity is opposite to average polarity of a voltage making the photodetecting TFT in the OFF state, to the gate electrode of the photodetecting TFT in an arbitrary period. Thus, it is possible to provide the image reading device which can suppress variation of a photodetecting TFT property (resistance value) which is observed in a short time.